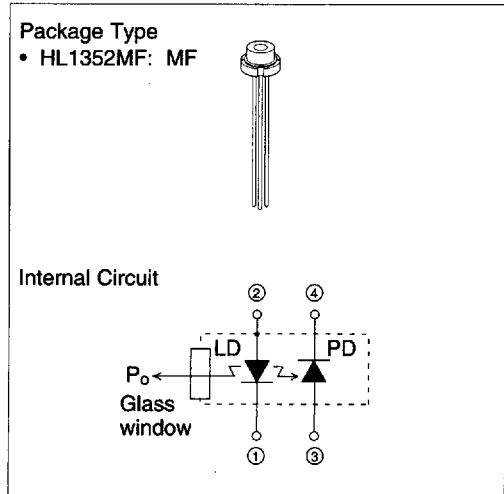


Description

The HL1352MF is a 1.3 μm InGaAsP distributed-feedback laser diode (DFB LD) with a multi-quantum well (MQW) structure. It is suitable as a light source for short and medium - range fiberoptic communication systems and other applied optical equipment. It has high optical power with low drive current and wide operating temperature range (-20 to +85°C). The compact package is suitable for module assembly.

Features

- Wide operating temperature range:
 $T_{opr} = -20$ to $+85^{\circ}\text{C}$
- High output power: 10 mW (Pulse)
 5 mW (CW)
- Low operating current:
 $I_{op} (P_O = 5 \text{ mW}) = 30 \text{ mA}$ (Typ. @ $T_C = 25^{\circ}\text{C}$)
 $I_{op} (P_O = 5 \text{ mW}) = 80 \text{ mA}$ (Typ. @ $T_C = 85^{\circ}\text{C}$)



Absolute Maximum Ratings ($T_C = 25^{\circ}\text{C}$)

Item	Symbol	Rated Value	Unit
Optical output power	P_O	10 (pulse)	mW
		5 (CW)	
LD reverse voltage	$V_R (LD)$	2	V
PD reverse voltage	$V_R (PD)$	15	V
PD forward current	$I_F (PD)$	1	mA
Operating temperature	T_{opr}	-20 to +85	$^{\circ}\text{C}$
Storage temperature	T_{stg}	-40 to +100	$^{\circ}\text{C}$

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Part

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Optical and Electrical Characteristics ($T_C = 25^\circ\text{C}$)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Threshold current	I_{th}	—	15	30	mA	
Optical output power	P_O	5	—	—	mW	Kink free
Slope efficiency	η	0.25	0.35	—	mW/mA	$T_C = 25^\circ\text{C}$
		0.10	0.15	—		$T_C = 85^\circ\text{C}$
Lasing wavelength	λ_p	1290	1310	1330	nm	$P_O = 5\text{ mW}$
Side-mode suppression ratio	S_r	30	38	—	nm	$P_O = 5\text{ mW}$
Beam divergence (parallel)	$\theta_{//}$	—	30	—	deg.	$P_O = 5\text{ mW}$, FWHM
Beam divergence (perpendicular)	θ_{\perp}	—	40	—	deg.	$P_O = 5\text{ mW}$, FWHM
Rise time	t_r	—	—	0.5	ns	10 to 90%
Fall time	t_f	—	—	0.5	ns	90 to 10%
Monitor current	I_S	100	—	—	μA	$P_O = 5\text{ mW}$, $V_{R(PD)} = 5\text{ V}$
PD dark current	I_{DARK}	—	—	350	nA	$V_{R(PD)} = 5\text{ V}$
PD capacitance	C_t	—	15	20	pF	$V_{R(PD)} = 5\text{ V}$, $f = 1\text{ MHz}$
Photosensitivity saturation voltage	$V_{R(S)}$	—	—	2	V	

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